

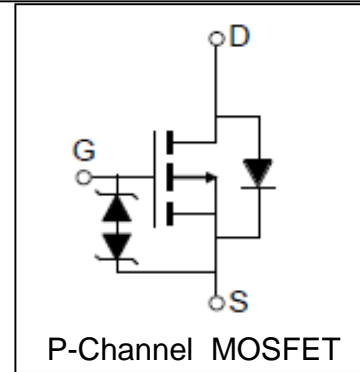
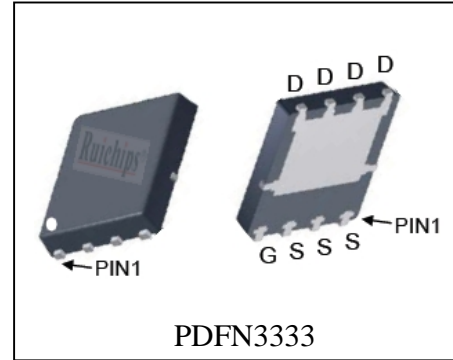
### Features

- -30V/-30A,  
 $R_{DS(ON)} = 12m$  (Typ.) @  $V_{GS} = -10V$   
 $R_{DS(ON)} = 20m$  (Typ.) @  $V_{GS} = -4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

### Applications

- Power Management
- Load Switching

### Pin Description



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
<b>Common Ratings</b> ( $T_C = 25^\circ C$ Unless Otherwise Noted)			
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	
$T_J$	Maximum Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$I_S$	Diode Continuous Forward Current	$T_C = 25^\circ C$ -30 <sup>①</sup>	A
<b>Mounted on Large Heat Sink</b>			
$I_{DP}$	300 $\mu s$ Pulse Drain Current Tested	$T_C = 25^\circ C$ -96 <sup>②</sup>	A
$I_D$	Continuous Drain Current ( $V_{GS} = -10V$ )	$T_C = 25^\circ C$ -30 <sup>①</sup>	A
		$T_C = 100^\circ C$ -19 <sup>①</sup>	
		$T_A = 25^\circ C$ -9.3 <sup>③</sup>	
		$T_A = 70^\circ C$ -7.5 <sup>③</sup>	
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$ 33	W
		$T_C = 100^\circ C$ 13	
		$T_A = 25^\circ C$ 3.5 <sup>③</sup>	
		$T_A = 70^\circ C$ 2.3 <sup>③</sup>	

<b>Mounted on Large Heat Sink</b>			
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3.8	°C/W
$R_{\theta JA}$ <sup>③</sup>	Thermal Resistance-Junction to Ambient	35	°C/W
<b>Drain-Source Avalanche Ratings</b>			
$E_{AS}$ <sup>④</sup>	Avalanche Energy, Single Pulsed	42	mJ

**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  Unless Otherwise Noted)

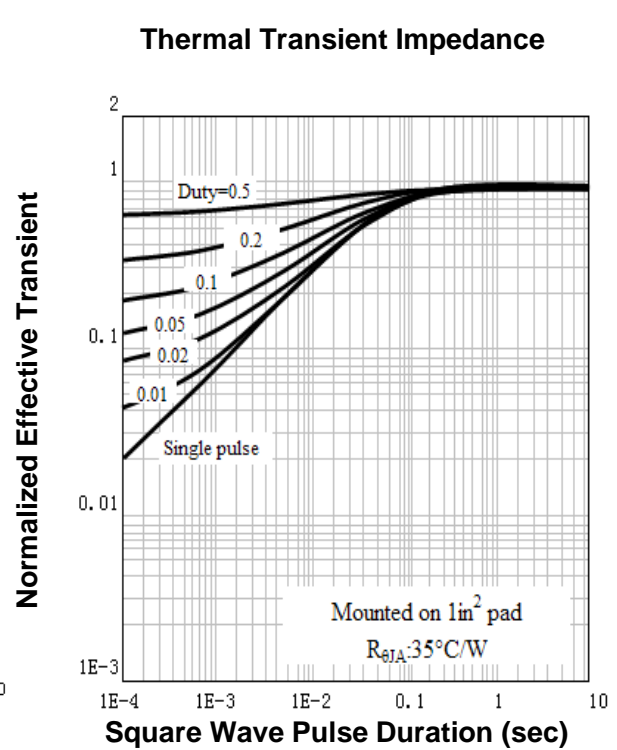
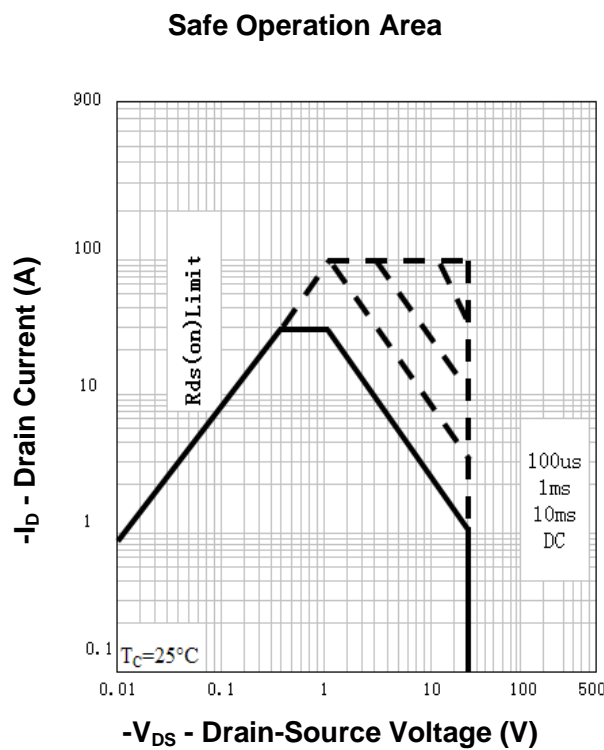
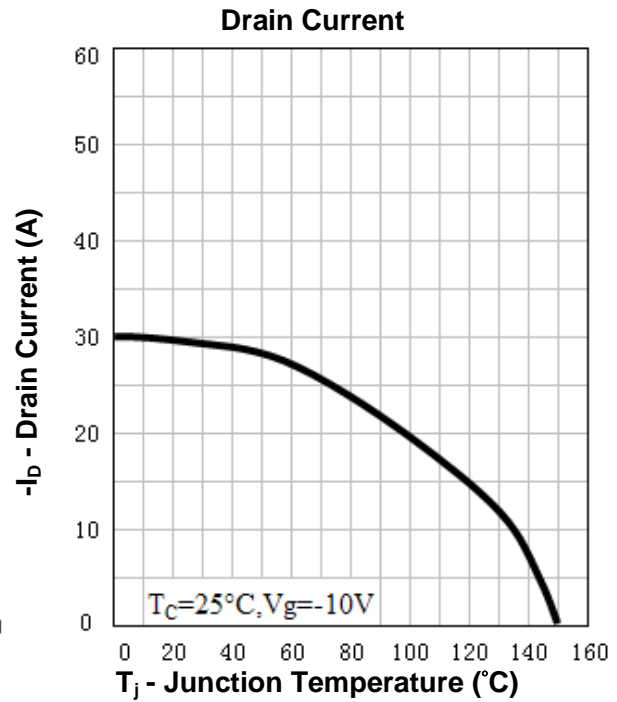
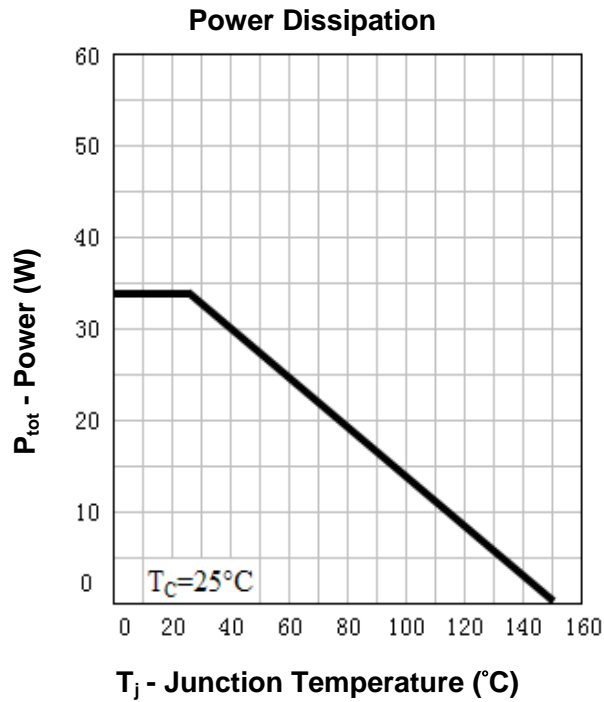
Symbol	Parameter	Test Condition	RU30L30M			Unit
			Min.	Typ.	Max.	
<b>Static Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			-1 -30	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-1	-	-2.5	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 10$	$\mu A$
$R_{DS(ON)}$ <sup>⑤</sup>	Drain-Source On-state Resistance	$V_{GS}=-10V, I_{DS}=-20A$		12	20	m $\Omega$
		$V_{GS}=-4.5V, I_{DS}=-16A$		20	34	m $\Omega$
<b>Diode Characteristics</b>						
$V_{SD}$ <sup>⑤</sup>	Diode Forward Voltage	$I_{SD}=-1A, V_{GS}=0V$			-1	V
$t_{rr}$	Reverse Recovery Time	$I_{SD}=-20A, dI_{SD}/dt=100A/\mu s$		45		ns
$Q_{rr}$	Reverse Recovery Charge			26		nC
<b>Dynamic Characteristics</b> <sup>⑥</sup>						
$R_G$	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.8		$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-15V,$ Frequency=1.0MHz		2300		pF
$C_{oss}$	Output Capacitance			250		
$C_{rss}$	Reverse Transfer Capacitance			160		
$t_{d(ON)}$	Turn-on Delay Time		$V_{DD}=-15V, R_L=0.75\Omega,$ $I_{DS}=-20A, V_{GEN}=-10V,$ $R_G=6\Omega$		17	
$t_r$	Turn-on Rise Time			32		
$t_{d(OFF)}$	Turn-off Delay Time			37		
$t_f$	Turn-off Fall Time			15		
<b>Gate Charge Characteristics</b> <sup>⑥</sup>						
$Q_g$	Total Gate Charge	$V_{DS}=-24V, V_{GS}=10V,$ $I_{DS}=-20A$		42		nC
$Q_{gs}$	Gate-Source Charge			9		
$Q_{gd}$	Gate-Drain Charge			13		

- Notes:
- ① Max current is limited by the source bonding.
  - ② Pulse width limited by safe operating area.
  - ③ When mounted on 1 inch square copper board,  $t \leq 10\text{sec}$ .
  - ④ Limited by  $T_{J\text{max}}$ ,  $I_{AS} = 13\text{A}$ ,  $V_{DD} = -24\text{V}$ ,  $R_G = 50\Omega$ , Starting  $T_J = 25^\circ\text{C}$ .
  - ⑤ Pulse test ; Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .
  - ⑥ Guaranteed by design, not subject to production testing.

## Ordering and Marking Information

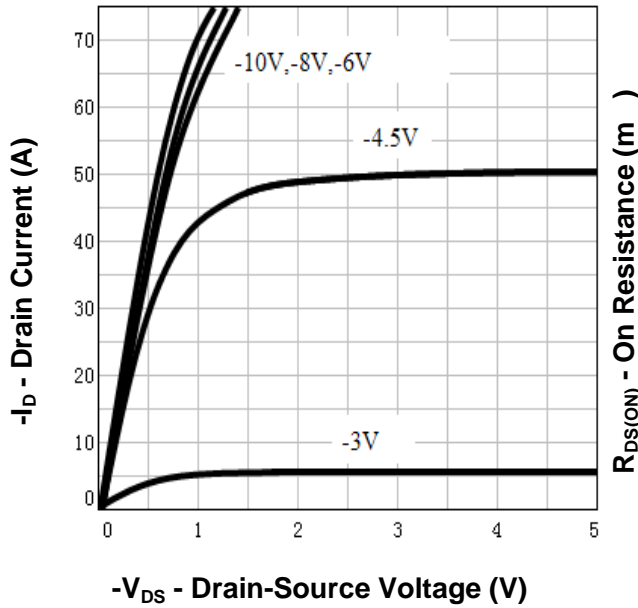
Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU30L30M	30L30	PDFN3333	Tape&Reel	5000	13''	12mm

**Typical Characteristics**

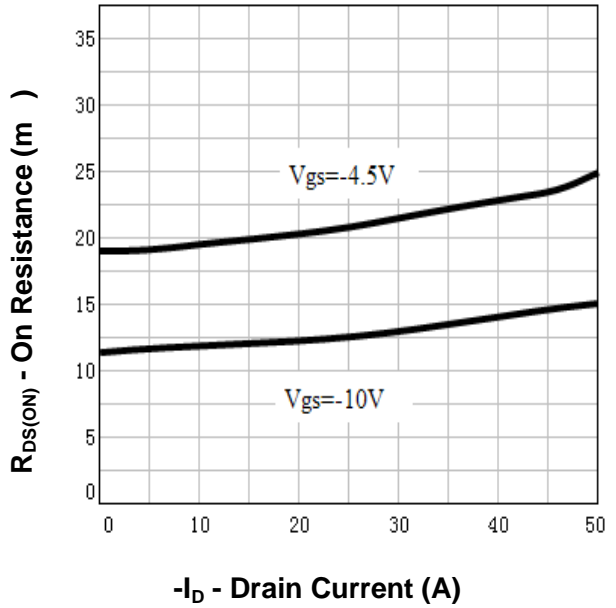


**Typical Characteristics**

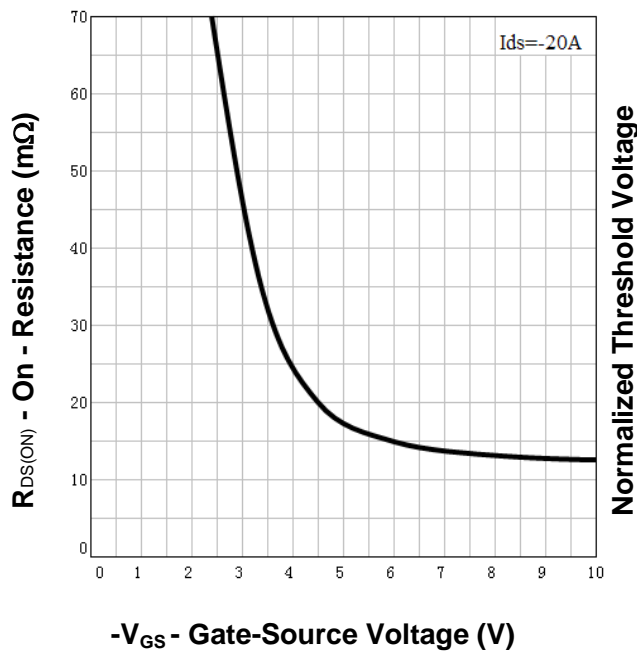
**Output Characteristics**



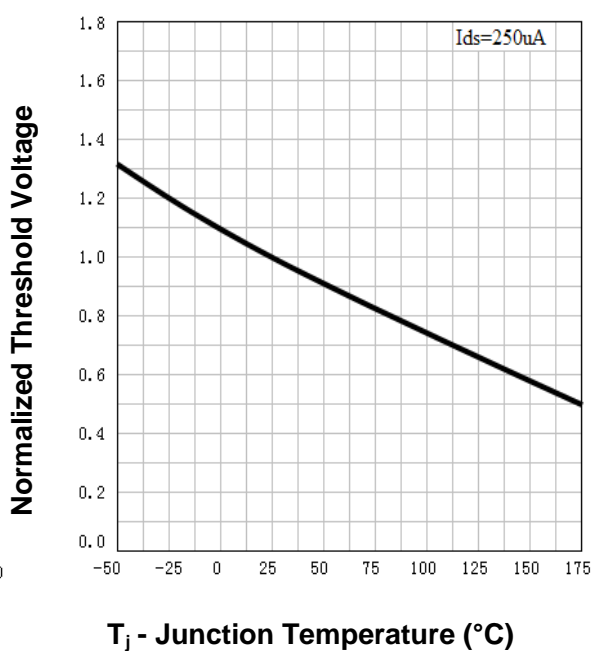
**Drain-Source On Resistance**



**Drain-Source On Resistance**

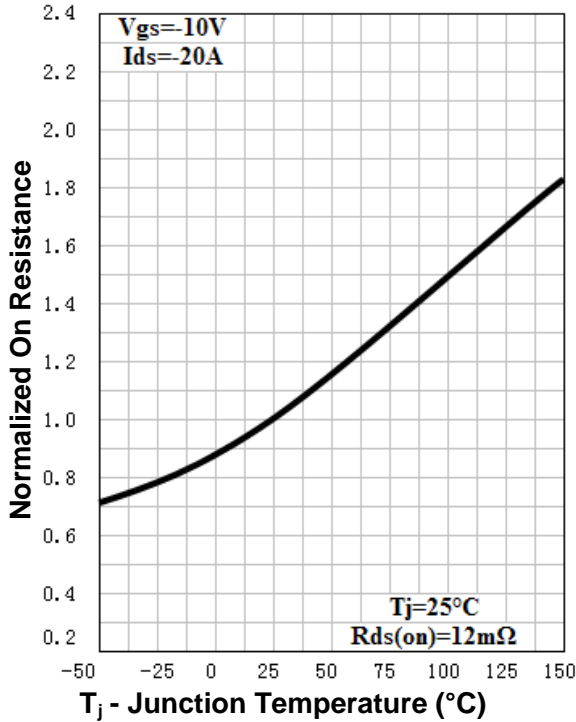


**Gate Threshold Voltage**

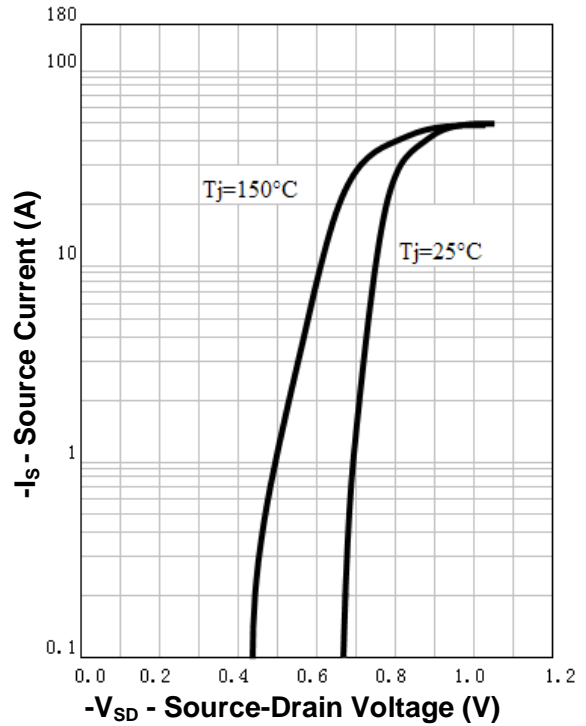


**Typical Characteristics**

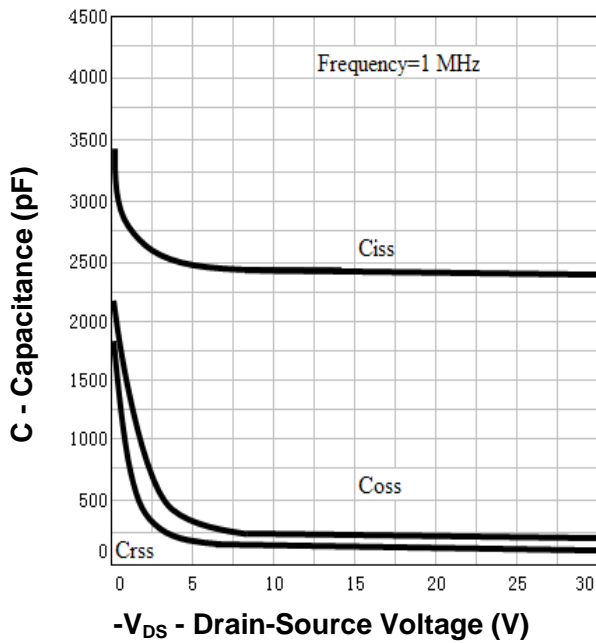
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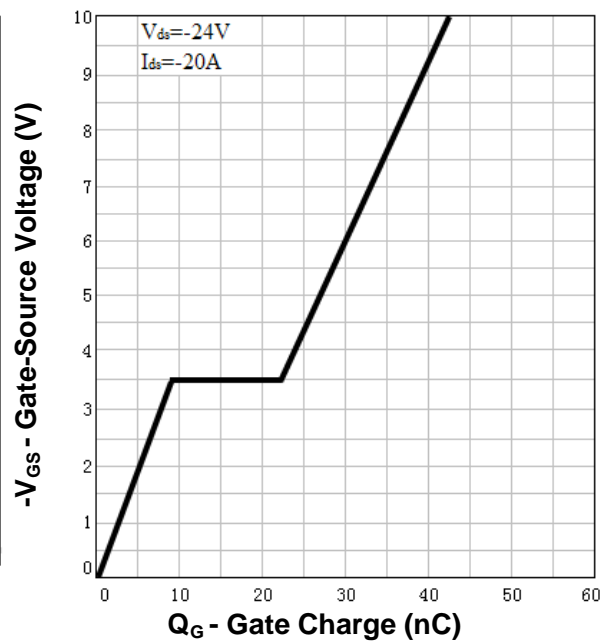
**Source-Drain Diode Forward**



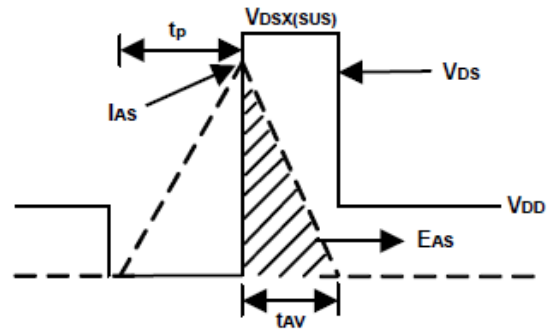
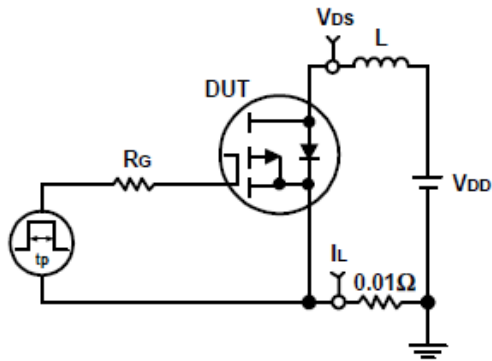
**Capacitance**



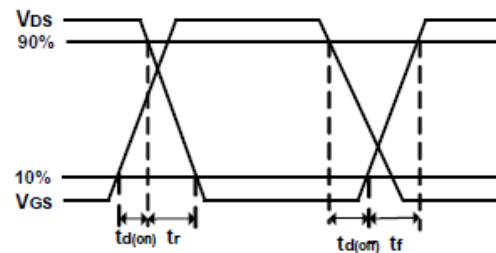
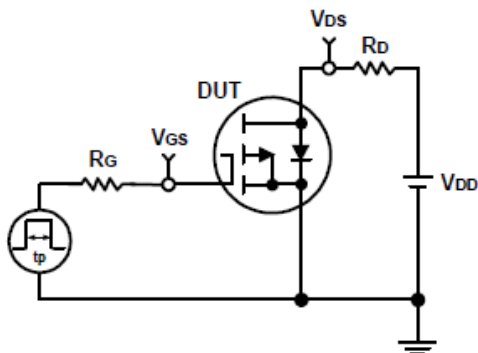
**Gate Charge**



**Avalanche Test Circuit and Waveforms**

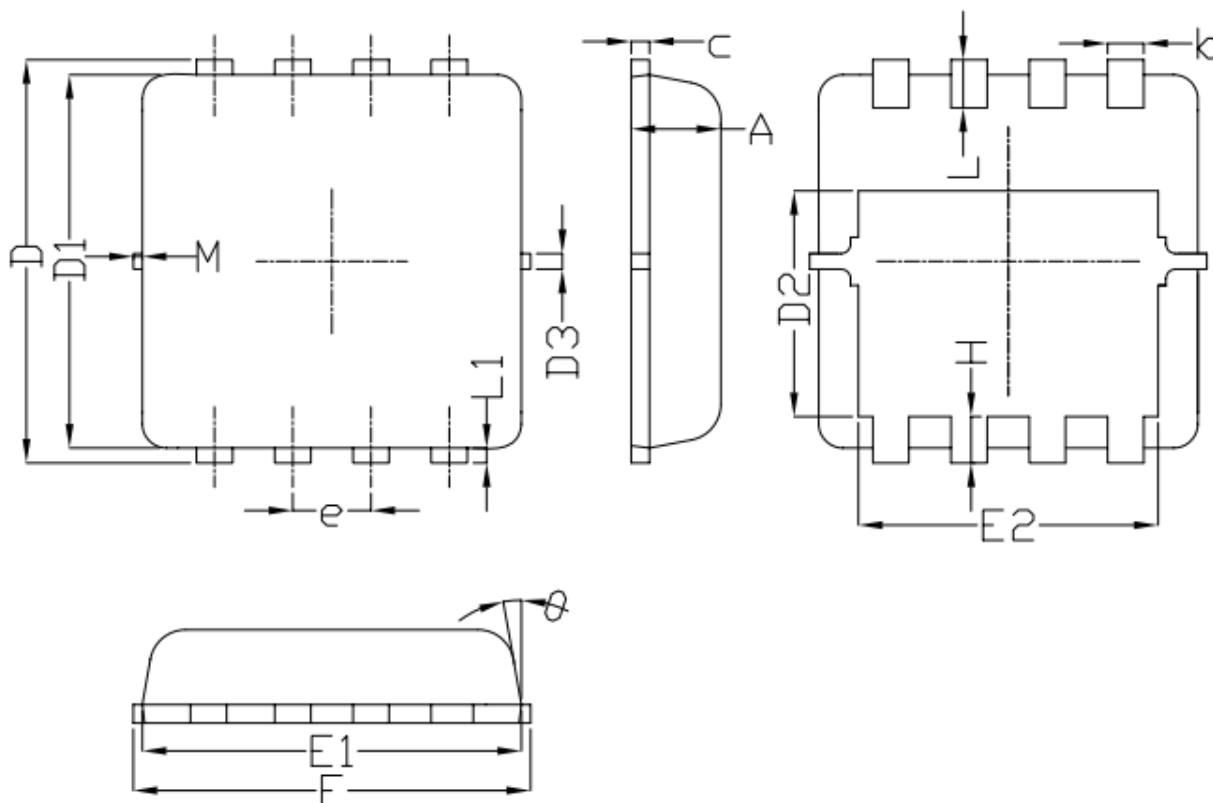


**Switching Time Test Circuit and Waveforms**



**Package Information**

PDFN3333



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031	E1	3.00	3.15	3.20	0.118	0.124	0.126
b	0.25	0.30	0.35	0.010	0.012	0.014	E2	2.39	2.49	2.59	0.094	0.098	0.102
c	0.10	0.15	0.25	0.004	0.006	0.010	e	0.65BSC			0.026BSC		
D	3.25	3.35	3.45	0.128	0.132	0.136	H	0.30	0.39	0.50	0.012	0.015	0.020
D1	3.00	3.10	3.20	0.118	0.122	0.126	L	0.30	0.40	0.50	0.012	0.016	0.020
D2	1.78	1.88	1.98	0.070	0.074	0.078	L1	-	0.13	-	-	0.005	-
D3	-	0.13	-	-	0.005	-		-	10°	12°	-	10°	12°
E	3.20	3.30	3.40	0.126	0.130	0.134	M	-	-	0.15			0.006



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